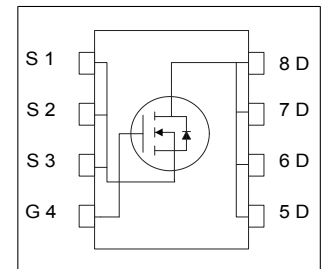
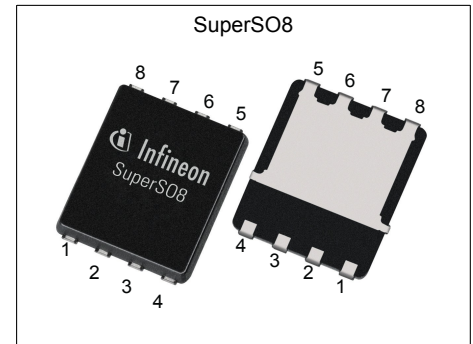


# MOSFET

## OptiMOS™3 Power-Transistor, 40 V

### Features

- Fast switching MOSFET for SMPS
- Optimized technology for DC/DC converters
- Qualified according to JEDEC<sup>1)</sup> for target applications
- N-channel; Normal level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- Superior thermal resistance
- 100% Avalanche tested
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}$	40	V
$R_{DS(on),max}$	1.9	m $\Omega$
$I_D$	204	A

Type / Ordering Code	Package	Marking	Related Links
BSC019N04NS G	PG-TDSON-8	019N04NS	-

<sup>1)</sup> J-STD20 and JESD22

## Table of Contents

Description .....	1
Maximum ratings .....	3
Thermal characteristics .....	3
Electrical characteristics .....	4
Electrical characteristics diagrams .....	6
Package Outlines .....	10
Revision History .....	12
Trademarks .....	12
Disclaimer .....	12

**1 Maximum ratings**  
 at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	204 129 29	A	$V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$ , $T_A=25\text{ °C}$ , $R_{thJA}=50\text{ K/W}^2)$
Pulsed drain current <sup>3)</sup>	$I_{D,pulse}$	-	-	816	A	$T_C=25\text{ °C}$
Avalanche current, single pulse <sup>4)</sup>	$I_{AS}$	-	-	50	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	295	mJ	$I_D=50\text{ A}$ , $R_{GS}=25\text{ }\Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	125 2.5	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$ , $R_{thJA}=50\text{ K/W}^2)$
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

**2 Thermal characteristics**

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	$R_{thJC}$	-	-	1	K/W	-
Thermal resistance, junction - case, top	$R_{thJC}$	-	-	18	K/W	-
Device on PCB, 6 cm <sup>2</sup> cooling area <sup>2)</sup>	$R_{thJA}$	-	-	50	K/W	-

<sup>1)</sup> Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C. For higher case temperature please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See Diagram 3 for more detailed information

<sup>4)</sup> See Diagram 13 for more detailed information

### 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	40	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2	-	4	V	$V_{DS}=V_{GS}$ , $I_D=85\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=40\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$ $V_{DS}=40\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	-	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.6	1.9	m $\Omega$	$V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$
Gate resistance	$R_G$	-	1.3	-	$\Omega$	-
Transconductance	$g_{fs}$	60	120	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=50\text{ A}$

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	6600	8800	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=20\text{ V}$ , $f=1\text{ MHz}$
Output capacitance	$C_{oss}$	-	1800	2400	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=20\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance	$C_{rss}$	-	70	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=20\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	22	-	ns	$V_{DD}=20\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=30\text{ A}$ , $R_G=1.6\text{ }\Omega$
Rise time	$t_r$	-	5.6	-	ns	$V_{DD}=20\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=30\text{ A}$ , $R_G=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	33	-	ns	$V_{DD}=20\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=30\text{ A}$ , $R_G=1.6\text{ }\Omega$
Fall time	$t_f$	-	6.6	-	ns	$V_{DD}=20\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=30\text{ A}$ , $R_G=1.6\text{ }\Omega$

**Table 6 Gate charge characteristics<sup>1)</sup>**

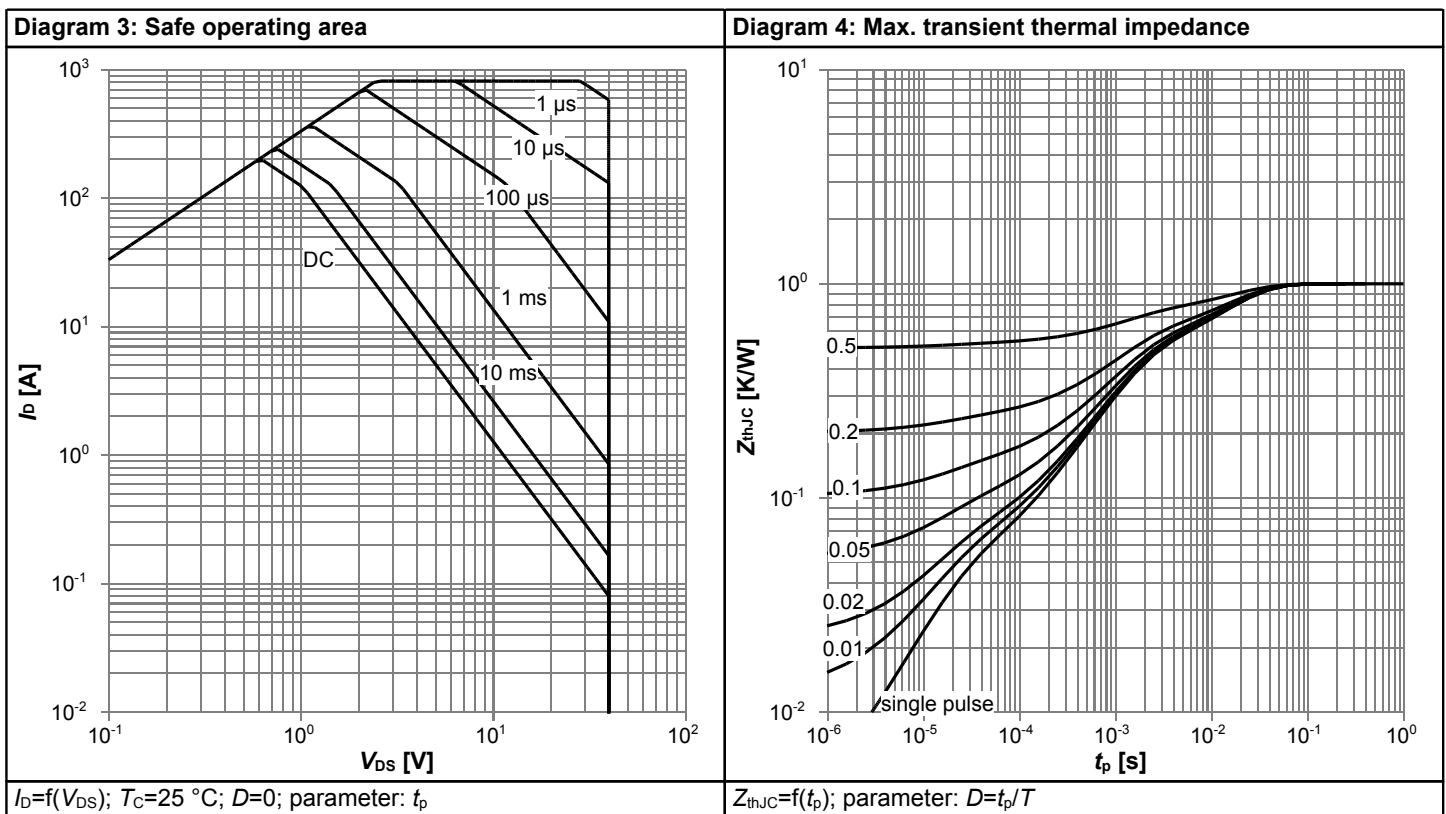
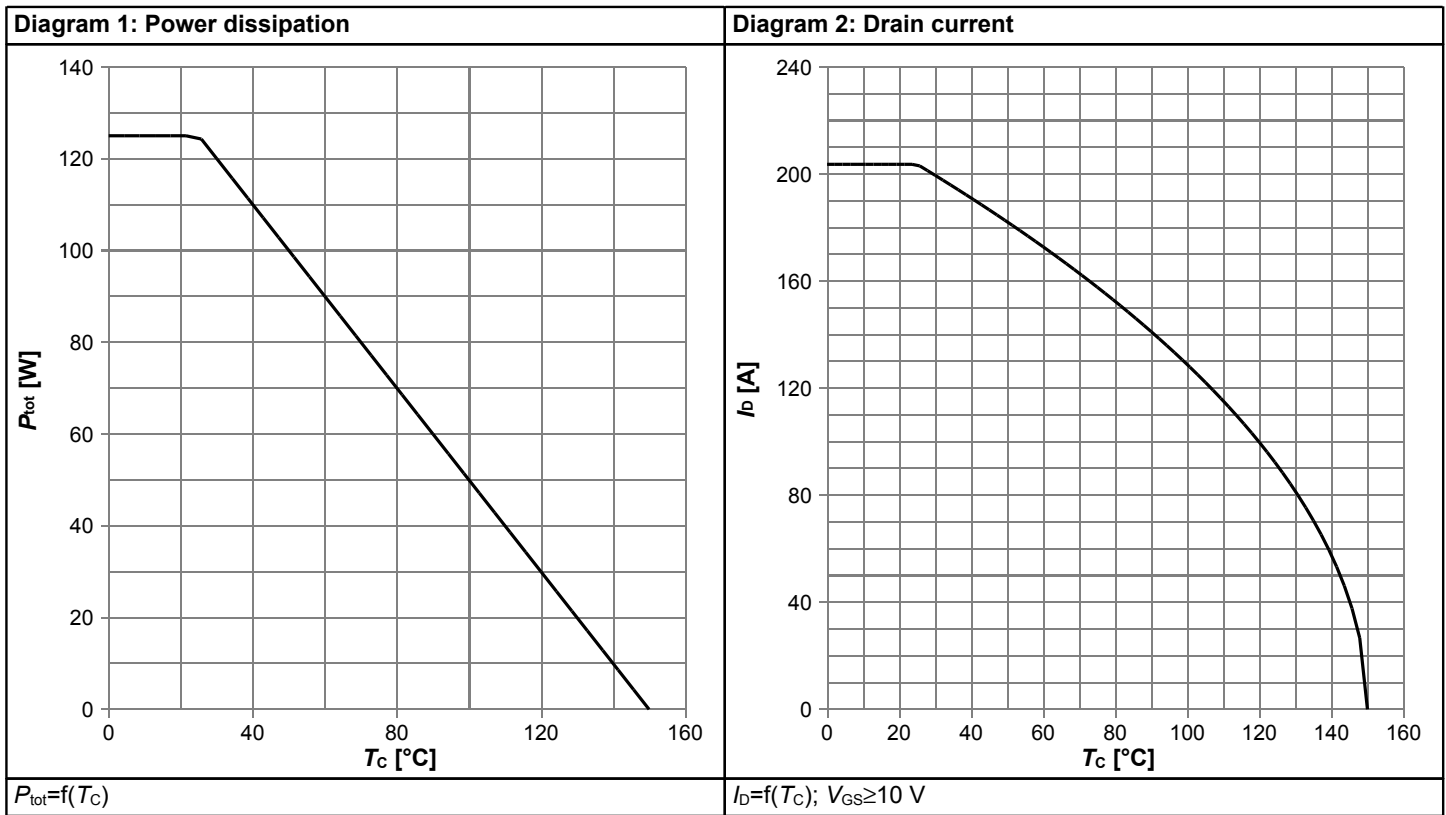
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	32	-	nC	$V_{DD}=20\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	20	-	nC	$V_{DD}=20\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	10	-	nC	$V_{DD}=20\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	$Q_{sw}$	-	22	-	nC	$V_{DD}=20\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	$Q_g$	-	81	108	nC	$V_{DD}=20\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.9	-	V	$V_{DD}=20\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	77	-	nC	$V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }10\text{ V}$
Output charge	$Q_{oss}$	-	66	-	nC	$V_{DD}=20\text{ V}$ , $V_{GS}=0\text{ V}$

<sup>1)</sup> See "Gate charge waveforms" for parameter definition

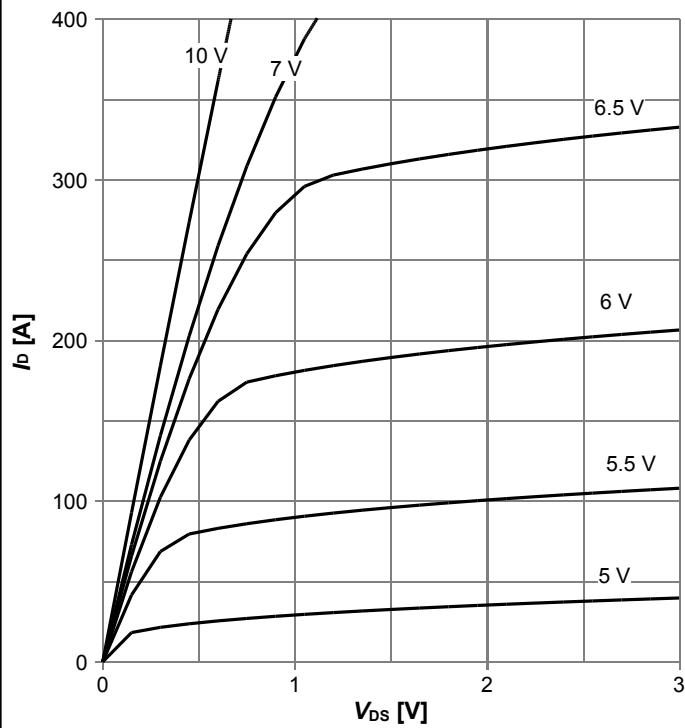
**Table 7 Reverse diode**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_S$	-	-	100	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	816	A	$T_C=25\text{ °C}$
Diode forward voltage	$V_{SD}$	-	0.85	1.2	V	$V_{GS}=0\text{ V}, I_F=50\text{ A}, T_j=25\text{ °C}$
Reverse recovery charge	$Q_{rr}$	-	100	-	nC	$V_R=20\text{ V}, I_F=I_S, di_F/dt=400\text{ A}/\mu\text{s}$

### 4 Electrical characteristics diagrams

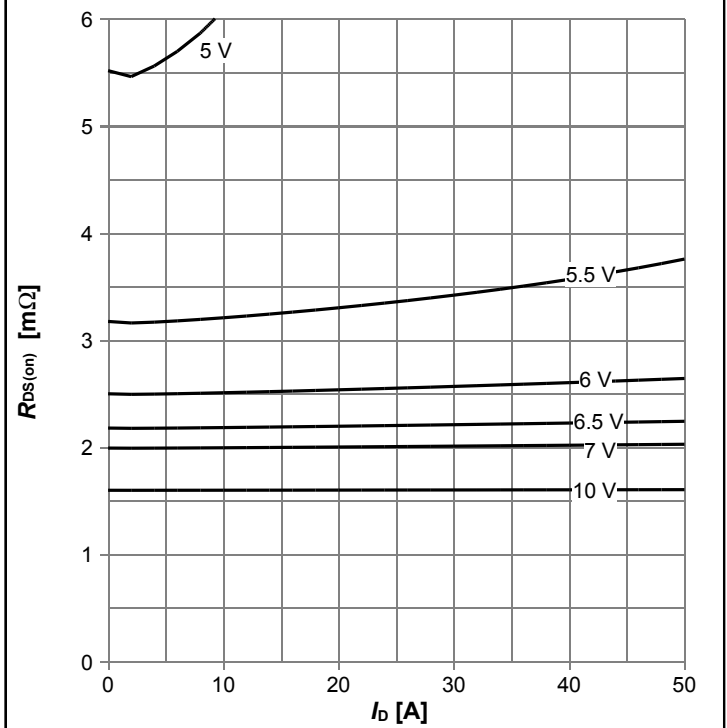


**Diagram 5: Typ. output characteristics**



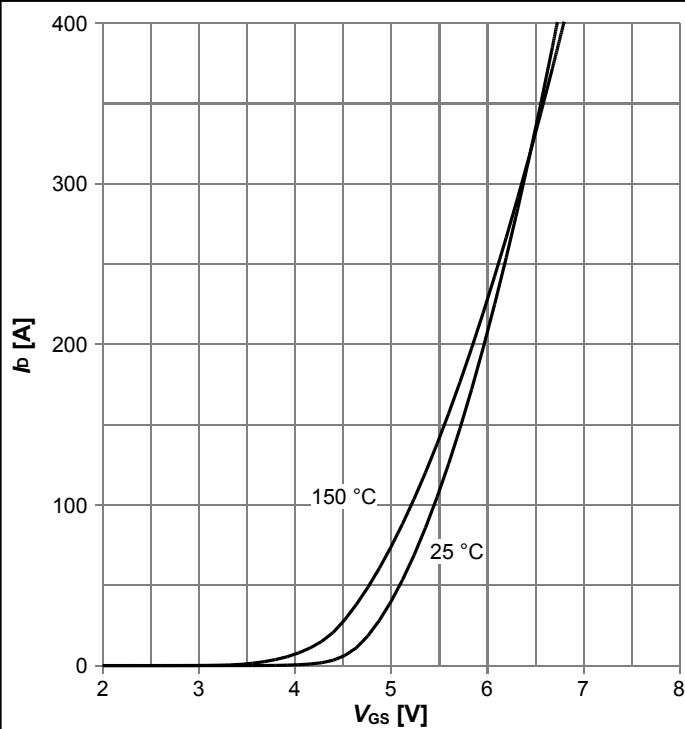
$I_D=f(V_{DS}); T_j=25\text{ °C};$  parameter:  $V_{GS}$

**Diagram 6: Typ. drain-source on resistance**



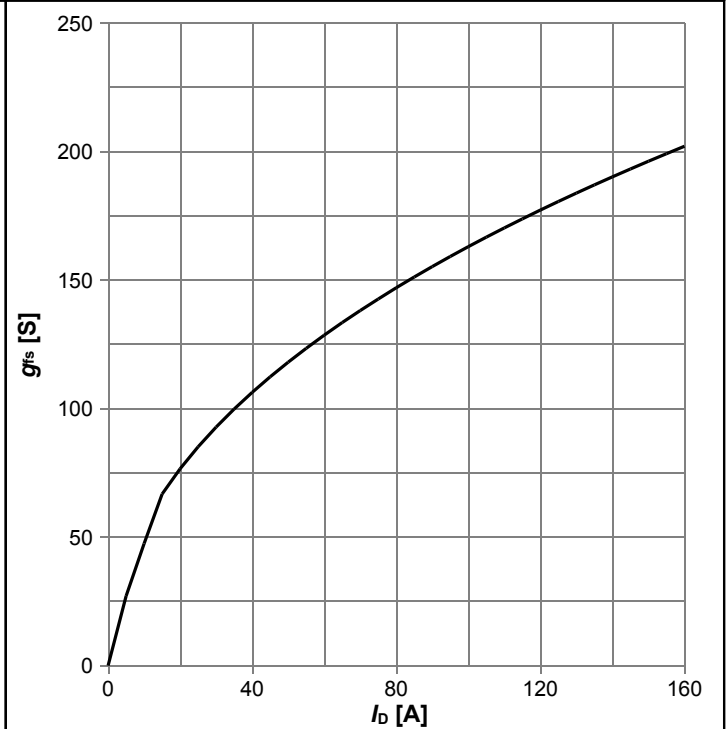
$R_{DS(on)}=f(I_D); T_j=25\text{ °C};$  parameter:  $V_{GS}$

**Diagram 7: Typ. transfer characteristics**



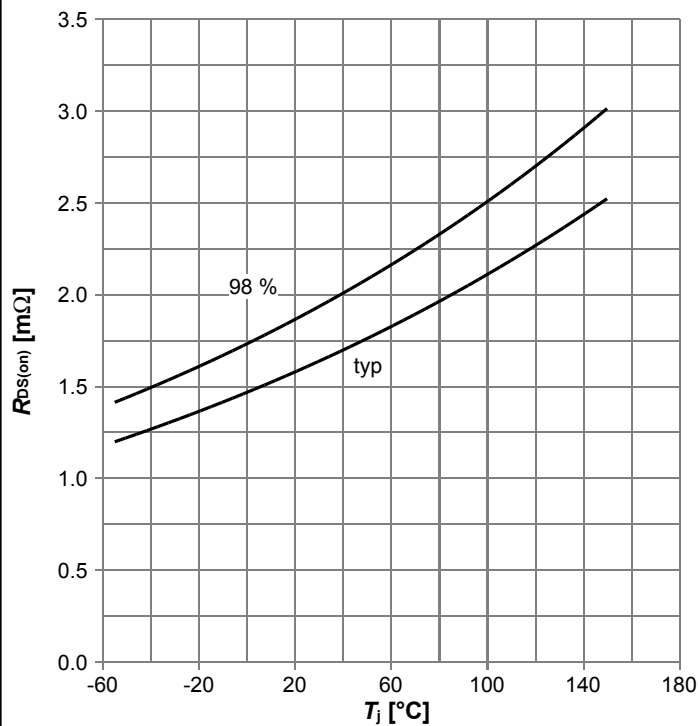
$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max};$  parameter:  $T_j$

**Diagram 8: Typ. forward transconductance**



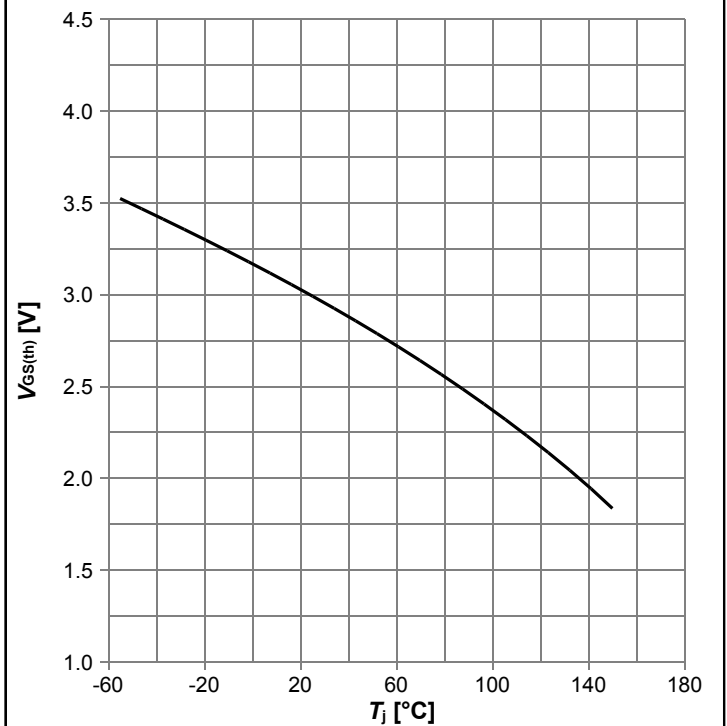
$g_{fs}=f(I_D); T_j=25\text{ °C}$

Diagram 9: Drain-source on-state resistance



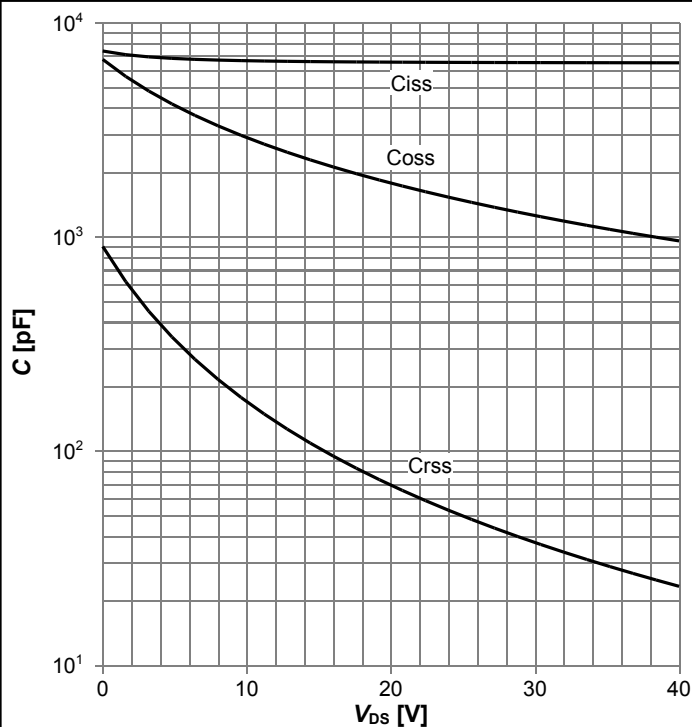
$R_{DS(on)}=f(T_j)$ ;  $I_D=50\text{ A}$ ;  $V_{GS}=10\text{ V}$

Diagram 10: Typ. gate threshold voltage



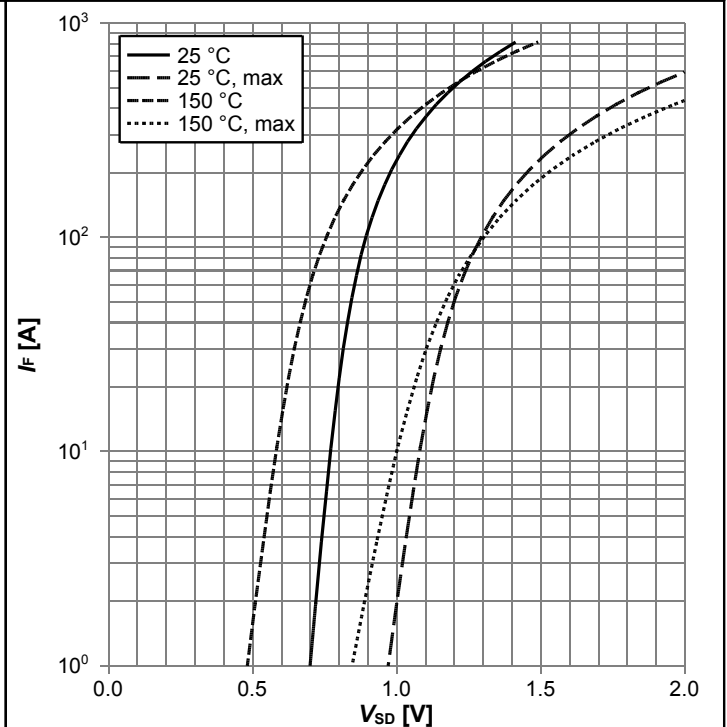
$V_{GS(th)}=f(T_j)$ ;  $V_{GS}=V_{DS}$ ;  $I_D=85\ \mu\text{A}$

Diagram 11: Typ. capacitances



$C=f(V_{DS})$ ;  $V_{GS}=0\text{ V}$ ;  $f=1\text{ MHz}$

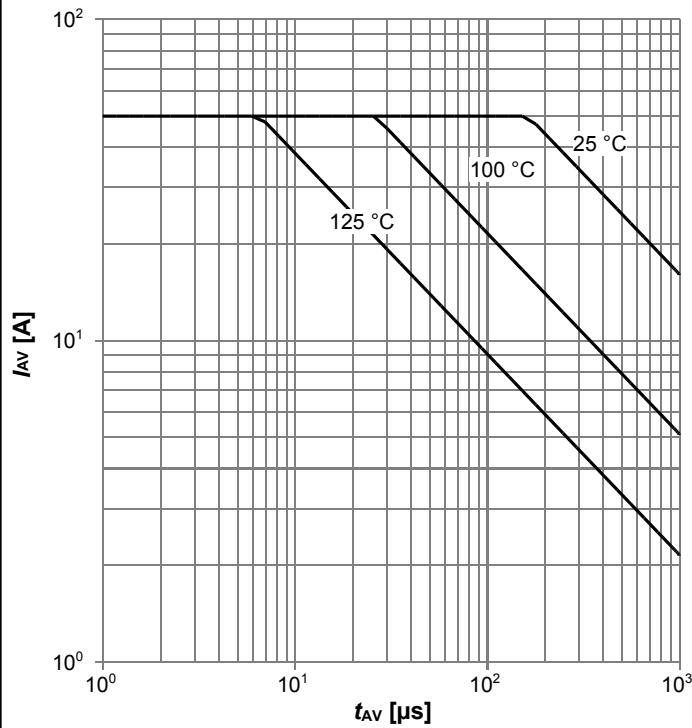
Diagram 12: Forward characteristics of reverse diode



$I_F=f(V_{SD})$ ; parameter:  $T_j$

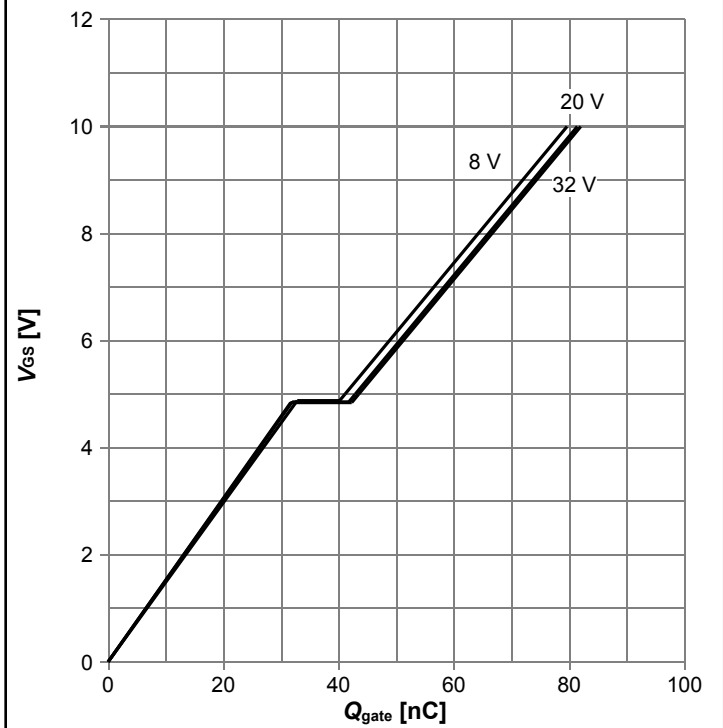


Diagram 13: Avalanche characteristics



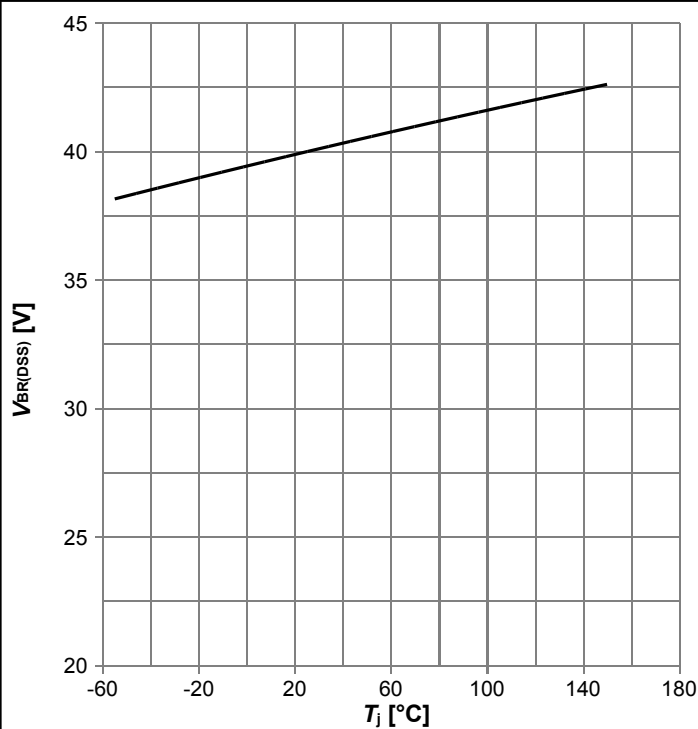
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j(start)}$

Diagram 14: Typ. gate charge



$V_{GS}=f(Q_{gate}); I_D=30 \text{ A pulsed}$ ; parameter:  $V_{DD}$

Diagram 15: Drain-source breakdown voltage

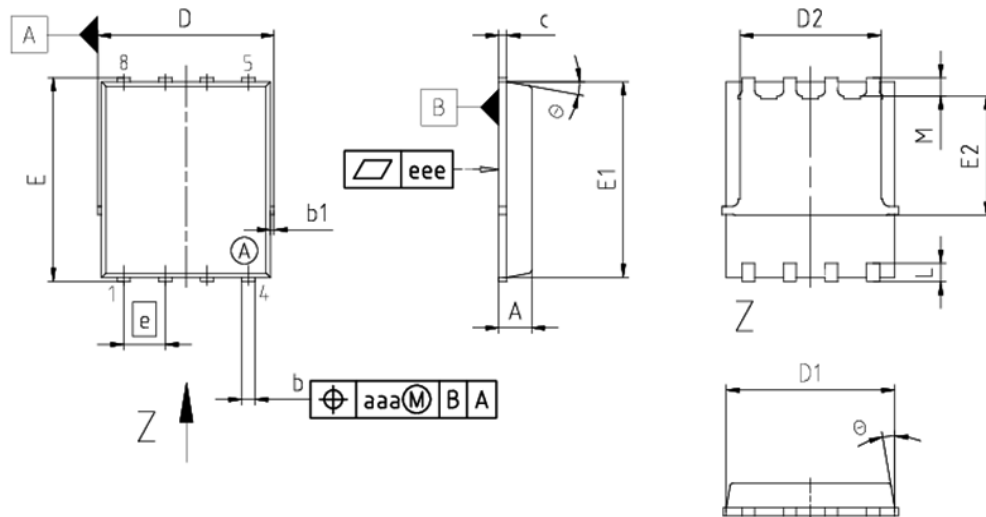


$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Diagram Gate charge waveforms



**5 Package Outlines**



DIM	MILLIMETERS	
	MIN	MAX
A	0.90	1.10
b	0.31	0.54
b1	0.02	0.22
c	0.15	0.35
D	5.15	5.49
D1	4.95	5.35
D2	3.70	4.40
E	5.95	6.35
E1	5.70	6.10
E2	3.40	3.80
e	1.27	
N	8	
L	0.45	0.71
M	0.45	0.75
theta	8.5°	12°
aaa	0.25	
eee	0.08	

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**Figure 1 Outline PG-TDSON-8, dimensions in mm**



## Revision History

BSC019N04NS G

**Revision: 2020-03-17, Rev. 2.1**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2018-04-09	Release of final version
2.1	2020-03-17	Update current rating

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